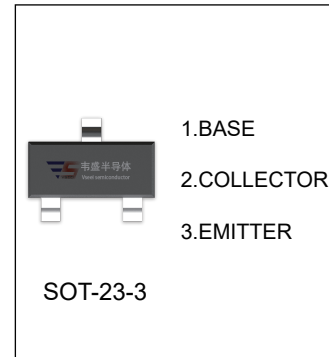


## 2SC2412K TRANSISTOR

### (NPN) FEATURES

- Low  $C_{ob}$ ,  $C_{ob} = 2.0 \text{ pF (Typ)}$ .



### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current	150	mA
$P_C$	Collector Power Dissipation	400	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	312.5	$^\circ\text{C/W}$
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}, I_C=0$	7			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60\text{V}, I_E=0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=7\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=6\text{V}, I_C=1\text{mA}$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.4	V
Transition frequency	$f_T$	$V_{CE}=12\text{V}, I_C=-2\text{mA}, f=100\text{MHz}$		150		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=12\text{V}, I_E=0, f=1\text{MHz}$		2.0	3.5	pF

### CLASSIFICATION OF $h_{FE}$

Rank	Q	R	S
Range	120 - 270	180 - 390	270 - 560
Marking	BQ	BR	BS

